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THE MEASUREMENT OF THE TEMPERATURE DRIFT OF THE MAGNETIC SENSITIVITY FOR THE HALL SENSOR

The annealing at the temperature of heat treatment of 403 K for the irradiated by the flow of electrons Ω=5•1015 el./cm2, with the energy of 10 MeV, single crystals n-Ge was discovered. In this annealing, the magnetic sensitivity of the material had been increasing. The temperature drift of the magnetic sensitivity was studied and the analytical expression was obtained for finding of the magnitude of the magnetic induction in the temperature range from 245-300 K. This expression can be used to determine the magnetic induction based on obtained signals of the Hall voltage and the voltage of electrical conductivity of the magnetically sensitive element regardless of the measurement temperature in the above range.

Primary author: Dr LUNIOV, Sergiy (Lutsk National Technical University)

Co-authors: Mr ZIMYCH, Andriy (Lutsk National Technical University); Mr MEGELA, Ivan (Institute of electron physics NAS of Ukraine); Ms UDOVYTSKA, Julia (Lutsk National Technical University); Prof. MASLYUK, Volodymyr (Institute of electron physics NAS of Ukraine)

Presenter: Mr ZIMYCH, Andriy (Lutsk National Technical University)

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